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applying a second high-frequency biasing power level equal to zero, after
ashing with the first high-frequency biasing power level.

- C2
41. (New) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, wherein the layer has an opening and a fence portion distending toward the upper portion of a surrounding edge of the opening, the processing method comprising:
- applying high-frequency power for biasing to the workpiece at a first power level;
 - raising the processing gas to a plasma; and
 - switching the high-frequency power for biasing applied to the workpiece from the first power level to a second power level lower than the first power level before the photoresist film becomes completely removed.
42. (New) A plasma processing method according to claim 41, wherein the fence portion is removed during applying high-frequency power for biasing to the workpiece at the first power level.
43. (New) A plasma processing method according to claim 41, wherein the first power level is switched to the second power level due to removing the fence portion.
44. (New) A plasma processing method according to claim 41, wherein the layer is an SiO₂ film formed at the workpiece.
45. (New) A plasma processing method according to claim 41, wherein the layer is an organic film formed at the workpiece.

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46. (New) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, comprising:
- etching the layer;
 - applying high-frequency power for biasing to the workpiece at a first power level and removing a fence portion distending toward the upper portion of a surrounding edge of an opening formed at the layer during the etching step;
 - raising the processing gas to a plasma; and
 - switching the high-frequency power for biasing applied to the workpiece from the first power level to a second power level lower than the first power level before the photoresist film becomes completely removed.
47. (New) A plasma processing method according to claim 46, wherein the layer is an SiO₂ film formed at the workpiece.
48. (New) A plasma processing method according to claim 46, wherein the layer is an organic film formed at the workpiece.
49. (New) A plasma processing method for removing a photoresist film formed at a workpiece placed within a processing chamber, comprising:
- applying high-frequency power for biasing to the workpiece;
 - raising the processing gas to a plasma;
 - ashing the photoresist while applying the high-frequency power for biasing to the workpiece; and
 - after the ashing step, stopping application of the high-frequency power for biasing before the photoresist film becomes completely removed,

while utilizing the same type of processing gas both before and after stopping application of the high-frequency power.

50. (New) A plasma processing method according to claim 49, wherein the photoresist film constitutes a mask used to form a specific pattern at an SiO₂ film formed at the workpiece.
51. (New) A plasma processing method according to claim 49, wherein the photoresist film constitutes a mask used to form a specific pattern at an organic film formed at the workpiece.
52. (New) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, wherein the layer has an opening and a fence portion distending toward the upper portion of a surrounding edge of the opening, the processing method comprising:
- applying high-frequency power for biasing to the workpiece;
 - raising the processing gas to a plasma; and
 - stopping application of the high-frequency power for biasing before the photoresist film becomes completely removed, while utilizing the same type of processing gas both before and after stopping application of the high-frequency power.
53. (New) A plasma processing method according to claim 52, wherein the fence portion is removed during applying high-frequency power for biasing to the workpiece at the first power level.

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54. (New) A plasma processing method according to claim 52, wherein the first power level is switched to the second power level due to removing the fence portion.
55. (New) A plasma processing method according to claim 52, wherein the layer is an SiO₂ film formed at the workpiece.
56. (New) A plasma processing method according to claim 52, wherein the layer is an organic film formed at the workpiece.
57. (New) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, comprising:
- etching the layer;
 - applying high-frequency power for biasing to the workpiece at a first power level and removing a fence portion distending toward the upper portion of a surrounding edge of an opening formed at the layer during the etching step;
 - raising the processing gas to a plasma; and
 - stopping application of the high-frequency power for biasing before the photoresist film becomes completely removed.
58. (New) A plasma processing method according to claim 57, wherein the layer is an SiO₂ film formed at the workpiece.
59. (New) A plasma processing method according to claim 57, wherein the layer is an organic film formed at the workpiece.
60. (New) A plasma processing method for removing a photoresist film having an opening pattern with a larger opening area than an opening area of a hole

formed at a specific layer of a workpiece, the opening of the hole contained in the opening pattern when the specific layer is etched to a middle portion thereof by utilizing the photoresist film as a mask, comprising:

applying high-frequency power for biasing to the workpiece;

raising the processing gas to a plasma;

ashing the photoresist while applying the high-frequency power for biasing to the workpiece; and

after the ashing step, stopping the application of the high-frequency power for biasing before the photoresist film becomes completely removed.

61. (New) A plasma processing method according to claim 60, wherein the specific layer is an SiO₂ film formed at the workpiece.
62. (New) A plasma processing method according to claim 60, wherein the specific layer is an organic film formed at the workpiece.

REMARKS

Claims 32-34 and 41-62 are pending in this application, with claims 32, 41, 46, 49, 52, 57, and 60 being independent claims. Claims 10-28 and 38-40 have been canceled. In place of the cancelled claims 10-28 and 38-40, claims 41-62 have been newly added, and claim 32 has been amended, to more clearly define features of the present invention. No new matter has been entered.

In the outstanding Office Action, the Examiner: rejected claims 32-34 under 35 U.S.C. § 102(b) as being anticipated by Berglund et al. (U.S. Patent No. 5,250,165); rejected claims 18-28 and 38-40 under 35 U.S.C. § 102(e) as being anticipated by Yang et al. (U.S. Patent No. 6,284,149); and rejected claims 10-17 under 35 U.S.C. § 103(a)

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